

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Specified at Operating Conditions
- Lead-Free

Benefits

- Reduced RFI and EMI
- · Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- · Reduced Parts Count

Description

International Rectifier's HFA15TB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA15TB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the ultrafast recovery diode product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The ultrafast recovery diode features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These ultrafast recovery diode advantages can help to significantly reduce snubbing, component count and heat sink sizes. The HFA15TB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Ultrafast, Soft Recovery Diode

 $V_{R} = 600V$ $V_F = 1.7V$ $Q_{rr}^* = 84nC$ $D_{I (rec)M}/dt = 188A/\mu s$ * 125°C



		Standard Pack			
Base part number	Package Type	Form	Quantity	Orderable Part Number	
HFA15TB60PbF	TO-220AC	Tube	50	HFA15TB60PbF	

Absolute Maximum Ratings

	Parameter	Max.	Units	
V_R	Cathode -to – Anode Voltage	600	V	
I _F @ T _C = 100°C	Continuous Forward Current	15		
Single Pulse Forward Current		150	Α	
I _{FRM}	Maximum Repetitive Forward Current	60		
P _D @T _C = 25°C Maximum Power Dissipation		74	14/	
P _D @T _C = 100°C Maximum Power Dissipation		29	W	
TJ	Operating Junction and		°C	
T _{STG}	Storage Temperature Range	-55 to + 150	°C	



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600				I _R = 100μA
			1.3	1.7	V	I _F = 15A See Fig. 1
V_{FM}	Max Forward Voltage		1.5	2.0	•	I _F = 30A
			1.2	1.6		$I_F = 30A , T_J = 125^{\circ}C$
	Max Reverse Leakage Current		1.0	10		$V_R = V_R$ Rated See Fig. 2
I _{RM}	Max Reverse Leakage Current		400	1000	μA	$T_J = 125^{\circ}C$, $V_R = 0.8 \times V_R$ Rated
C_T	Junction Capacitance		25	50	pF	$V_R = 200V$ See Fig. 3
Ls	Series Inductance		8.0		nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ TJ = 25°C (unless otherwise specified)

	Parameter		Тур.	Max.	Units	Conditions	
trr			19			$I_F = 1.0A$, dif/dt = 200A/ μ s, $V_R = 30V$	
trr1	Reverse Recovery Time See Fig. 5		42	60	ns	T _J = 25°C	
trr2			74	120		T _J = 125°C	
I _{RRM1}	Peak Recovery Current See Fig. 6		4.0	6.0	Δ	T _J = 25°C I _F =15A	
I _{RRM2}	l eak Necovery Current See Fig. 0		6.5	10		$T_J = 125^{\circ}C V_R = 200V$	
Q _{rr1}	Daviere Danis on Charge Can Fig 7		84	180	0	$T_J = 25^{\circ}C$ di/dt = 200A/µs	
Q _{rr2}	Reverse Recovery Charge See Fig.7		241	600	nC	T _J = 125°C	
di _{(rec)M/} dt1	Peak Rate of Fall of Recovery Current		188		Α /:	T _J = 25°C	
di _{(rec)M/} dt2	During tb See Fig.8		160		A/µs	T _J = 125°C	

Thermal -Mechanical Characteristics

	Parameter	Min.	Тур.	Max.	Units	
T _{lead} ①	Lead Temperature			300	°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case			1.7		
R _{0JA} ②	Thermal Resistance, Junction to Ambient			80	K/W	
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink		0.50			
۸,4	Mainlet		2.0		g	
Wt	Weight		0.07		(oz)	
т	Mounting Torons	6.0		12	Kg-cm	
I	Mounting Torque	5.0		10	lbf•in	

- ① 0.063 in. from Case (1.6mm) for 10 sec
- ② Typical Socket Mount
- 3 Mounting Surface, Flat, Smooth and Greased



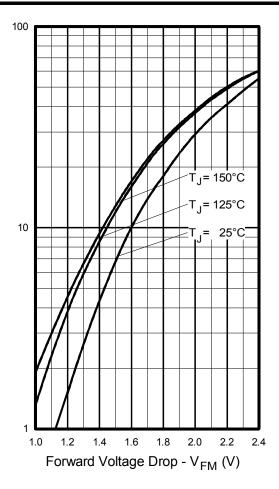


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

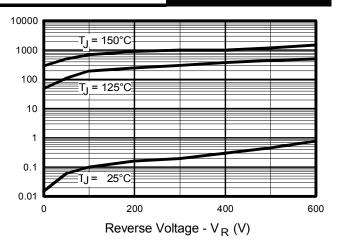


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

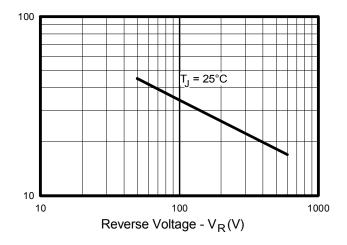


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

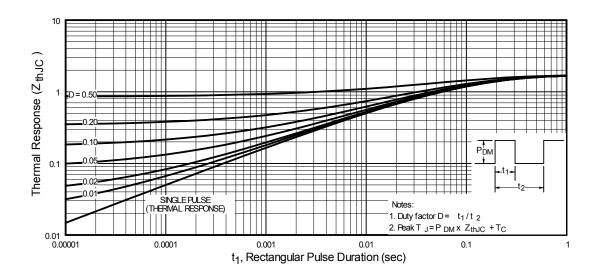


Fig. 4 - Maximum Thermal Impedance Zthjc Characteristics



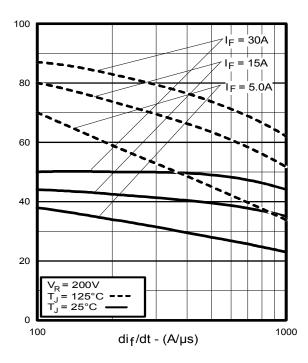


Fig. 5 - Typical Reverse Recovery vs. dif/dt

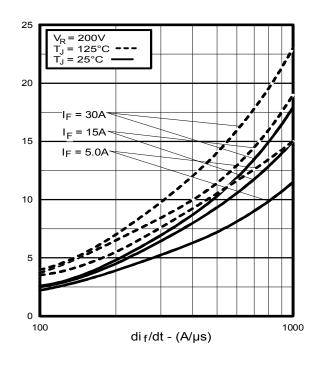


Fig. 6 - Typical Recovery Current vs. dif/dt

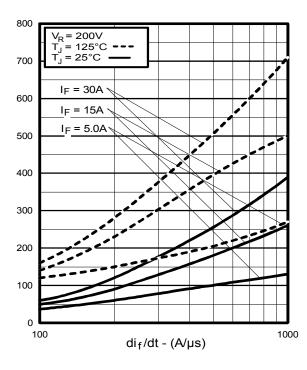


Fig. 7 - Typical Stored Charge vs. dif/dt

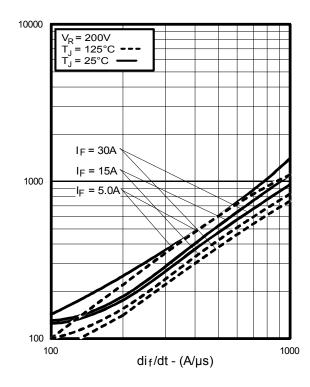
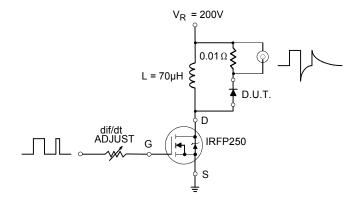
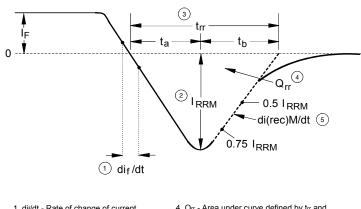


Fig. 8 - Typical di(rec)M/dt vs. dif/dt



REVERSE RECOVERY CIRCUIT





- 1. dif/dt Rate of change of current
- through zero crossing
 2. IRRM Peak reverse recovery current
- IRRM Peak reverse recovery current
 Irr Reverse recovery time measured
 from zero crossing point of negative
 going IF to point where a line passing
 through 0.75 IRRM and 0.50 IRRM
 extrapolated to zero current
- 4. Qrr Area under curve defined by trr and IRRM

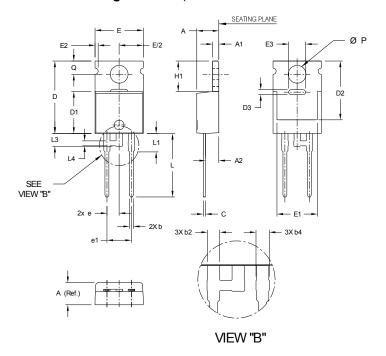
5. di_{(rec)M}/dt - Peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions



TO-220AC Package Outline (Dimensions are shown in millimeters (inches))

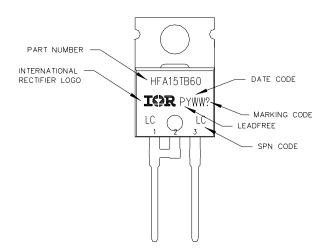


SYMBOL	MIN.	NOM.	MAX.		
А	3.56	4.57	4.83		
A1	1.14	1.27	1.40		
A2	2.03	2.77	2.92		
b	0.38	0.81	1.01		
b2	1.17	1.27	1.37		
b4	1.25	1.35	1.45		
С	0.36	0.46	0.61		
D	14.32	15.00	16.51		
D1	8.38	8.69	9.02		
D2	11.68	12.19	12.88		
D3	0.82	1.02	1.22		
E	9.65	10.00	10.67		
E1	6.86	8.39	8.89		
E2			0.76		
E3 3.30		3.50	3.70		
е	2.54 BASIC				
e1	E)	.08 BASI	C		
H1	5.84	6.31	6.86		
L	12.70	13.16	14.73		
L1	3.56	3.83	4.06		
L3	2.31	2.56	2.81		
L4	0.76	1.01	1.27		
ØΡ	3.54	3.68	4.08		
Q	2.54	2.74	3.42		

NOTES:

- 1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS.

TO-220AC Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/



Qualification Information[†]

	Industrial			
Qualification Level	(per JEDEC JESD47F) ††			
Moisture Sensitivity Level	TO-220AC	N/A		
RoHS Compliant	Yes			

- † Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/
- †† Applicable version of JEDEC standard at the time of product release.



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